



DOCUMENT CHANGE REQUEST

DCR number 623 Changes required for: General

Originator: S Jeffery

Date: 2010/10/25

Date sent: 2010/09/20

Organisation: ESA/ESTEC

Status: IMPLEMENTED

Title: Transistors, Power, MOSFET, N-Channel, RAD-HARD, based on Type STRH100N10FSY3

Number: 5205/021

Issue: 1

Other documents affected:

Page:

Page 15, Paragraph 2.11.2

Paragraph:

Page 15, Paragraph 2.11.2

Original wording:

Proposed wording:

Correct the following editorial error which appears in Electrical Measurements for Total Dose Radiation Testing: The Drift Values of the Gate-to-Source Leakage Currents (1 and 2) shall be corrected from "+150nA / -150nA" to "+15nA / -15nA" respectively.

Justification:

An editorial error in STMicroelectronics' detail spec has been inadvertently copied into Issue 1 of ESCC 5201/021.

Attachments:

N/A

Modifications:

N/A

Approval signature:

Date signed:

2010-10-25